

REMARKS

Claims 21-63 are presented herein for examination. Claims 21-56 were withdrawn from consideration in the immediate parent application as being non-elected species of a first invention, the Examiner alleging that there was no generic Claim. A copy of the Restriction is provided herewith as Attachment 'A'.

Claims 57-63 are new Claims directed to the invention and species of Claims 29-41. Such new Claims are fully supported by the specification and accompanying figures. For example, Figs. 2-4 and the associated text in the specification. In addition, Applicant has amended both the Title and the Abstract of the Disclosure.

Respectfully submitted,

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 09/641,879
Priority Filing Date August 17, 2000
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Assignee Micron Technology, Inc.
Priority Group Art Unit 2813
Priority Examiner Y. Huyhn
Attorney's Docket No. MI22-1859
Title: DRAM Circuitry, Method Of Forming A Field Emission Device, And Field
Emission Device (As Amended)

**VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
PRELIMINARY AMENDMENT**

The Title is amended as follows. Underlines indicate insertions and ~~strikeouts~~
indicate deletions.

~~Method Of Depositing An Aluminum Nitride Comprising Layer Over A~~
~~Semiconductor Substrate, Method Of Forming DRAM Circuitry, DRAM Circuitry,~~
Method Of Forming A Field Emission Device, And Field Emission Device

The Abstract of the Disclosure is amended as follows. Underlines indicate
insertions and ~~strikeouts~~ indicate deletions.

The invention is a ~~method of depositing an aluminum nitride comprising~~
~~layer over a semiconductor substrate, a method of forming DRAM circuitry,~~
DRAM circuitry, a method of forming a field emission device, and a field
emission device. ~~In one aspect, a method of depositing~~ Depositing an aluminum
nitride comprising layer over a ~~semiconductor~~ substrate includes positioning a

semiconductor substrate within a chemical vapor deposition reactor. Ammonia and at least one of triethylaluminum and trimethylaluminum are fed to the reactor while the substrate is at a temperature of about 500°C or less and at a reactor pressure from about 100 mTorr to about 725 Torr effective to deposit a layer comprising aluminum nitride over the substrate at such temperature and reactor pressure. In one aspect, such layer is utilized as a cell dielectric layer in DRAM circuitry. ~~In one aspect, such~~ Such layer is deposited over emitters of a field emission display. The invention contemplates DRAM and field emission devices utilizing such layer and alternate layers.

The Claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Cancel Claims 1-20.

Add Claims 57-63.

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